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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

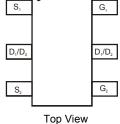
- Low Gate Charge
- Low R_{DS(ON)}:
 - 24mΩ @ V_{GS} = 4.5V
 - 28mΩ @ V_{GS} = 2.5V
 - 34mΩ @ V_{GS} = 1.8V
- Low Input/Output Leakage
- ESD Protected up to 2kV HBM
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

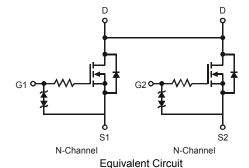
- Case: SOT26
- Case Material Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe Solderable per MIL-STD-202, Method 208 (e3)
- Terminal Connections: See Diagram
- Weight: 0.0008 grams (approximate)







SOT26



Top View

Top View Pin Configuration

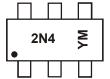
Ordering Information (Note 4)

Part Number	Case	Packaging
DMG6968UDM-7	SOT26	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



2N4 = Product Type Marking Code YM = Date Code Marking

Y = Year (ex: W = 2009)

M = Month (ex: 9 = September)

Date Code Kev

 ato codo rtoj												
Year	2008		2009	2010		2011	2012	2	2013	2014		2015
Code	V		W	Х		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	20	V
Gate-Source Voltage (Note 5)	V _{GSS}	±12	V
Drain Current (Note 6) Continuous $T_A = -T_A = -T$	l _D	6.5 5.2	А
Pulsed Drain Current (Note 7)	I _{DM}	30	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P _D	0.85	W
Thermal Resistance, Junction to Ambient (Note 6) t ≤10s	$R_{ hetaJA}$	147	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 5. AEC-Q101 VGS maximum is $\pm 9.6 \text{V}.$
- 6. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t \leq 10s. 7. Repetitive Rating, pulse width limited by junction temperature.

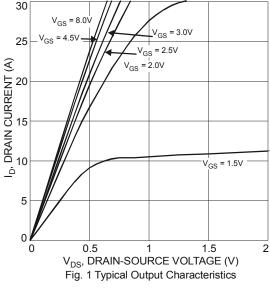
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

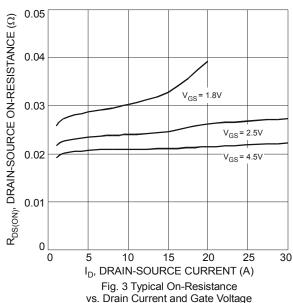
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
STATIC CHARACTERISTICS			•				
Drain-Source Breakdown Voltage	BV _{DSS}	20	_		>	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	V _{DS} = 20V, V _{GS} = 0V	
Gate-Body Leakage Current	I _{GSS}	_	_	±10	μΑ	$V_{DS} = 0V, V_{GS} = \pm 10V$	
Gate-Source Breakdown Voltage	BV _{SGS}	±12	_	_	V	$V_{DS} = 0V, I_G = \pm 250 \mu A$	
Gate Threshold Voltage	V _{GS(th)}	0.5	_	0.9	V	V _{DS} = V _{GS} , I _D = 250μA	
Static Drain-Source On-Resistance (Note 8)	R _{DS} (ON)		17 20 26	24 28 34	mΩ	$V_{GS} = 4.5V$, $I_D = 6.5A$ $V_{GS} = 2.5V$, $I_D = 5.5A$ $V_{GS} = 1.8V$, $I_D = 3.5A$	
Forward Transfer Admittance	Y _{FS}	_	8	_	S	V _{DS} = 10V, I _D = 5A	
Diode Forward Voltage (Note 8)		_	0.7	1.0	V	I _S = 2.25A, V _{GS} = 0V	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}		143	_	pF		
Output Capacitance	Coss		74	_	pF	$V_{DS} = 10V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	29	_	pF	11 - 1.0IVID2	
Gate Resisitance	R_{G}	_	202	_	Ω	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz	
SWITCHING CHARACTERISTICS (Note 9)							
Total Gate Charge	Q_g		8.8	_	nC		
Gate-Source Charge	Q_{gs}		1.4		nC	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 6.5A$	
Gate-Drain Charge	Q_{gd}		3.0		nC		
Turn-On Delay Time	t _{D(on)}	_	53	_	ns		
Turn-On Rise Time	t _r	_	78	_	ns	V _{DD} = 10V, V _{GS} = 4.5V,	
Turn-Off Delay Time	t _{D(off)}	_	562	_	ns	$R_L = 10\Omega$, $R_G = 6\Omega$	
Turn-Off Fall Time	t _f		234		ns		

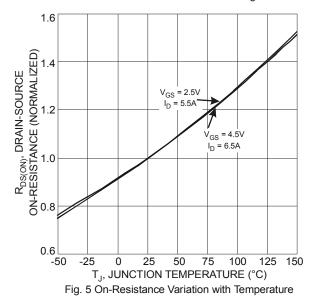
Notes:

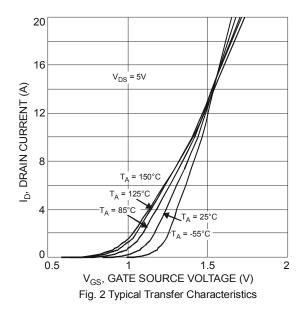
- 8. Test pulse width t = 300ms.
- 9. Guaranteed by design. Not subject to production testing.











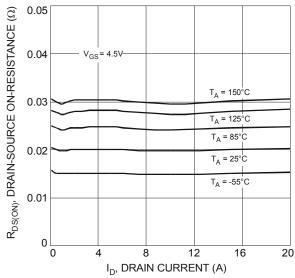


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

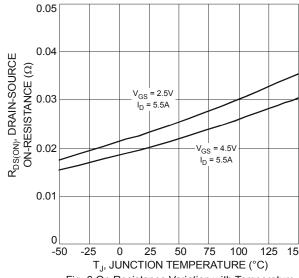


Fig. 6 On-Resistance Variation with Temperature



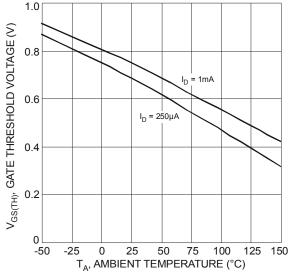
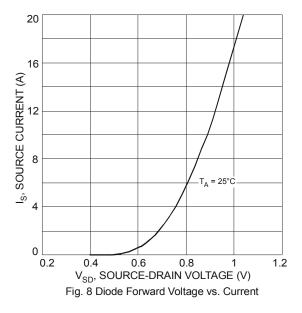
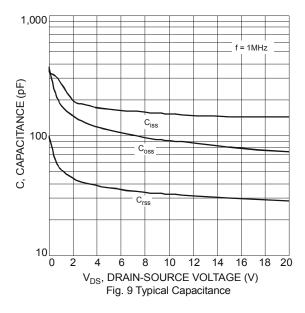


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





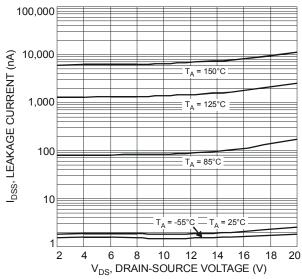


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

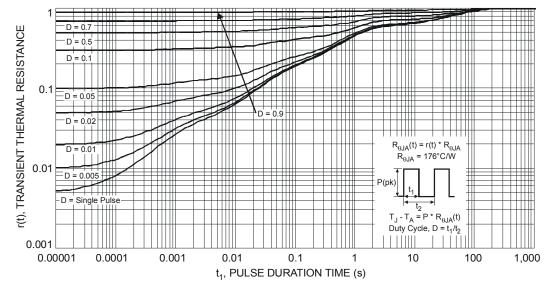
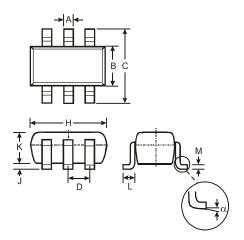


Fig. 11 Transient Thermal Response



Package Outline Dimensions

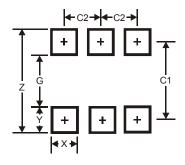
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT26							
Dim	Min	Max	Тур					
Α	0.35	0.50	0.38					
В	1.50	1.70	1.60					
С	2.70	3.00	2.80					
D	_	_	0.95					
Н	2.90	3.10	3.00					
J	0.013	0.10	0.05					
K	1.00	1.30	1.10					
L	0.35	0.55	0.40					
M	0.10	0.20	0.15					
α 0°		8°	_					
All Dimensions in mm								

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95



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